

Preliminary

13.75 - 14.5 GHz 1W MMIC

FEATURES

- P₁ dB: 30 dBm
- Small Signal Gain: 30 dB
- IP3: 39 dBm
- Match to 50 Ω Operation
- Bias condition: 750 mA @ 8 V

DESCRIPTION

The TC4535 is a 4 stage PHEMT MMIC power amplifier. It is designed for use in low cost, high volume, Ku band applications. The MMIC is matched to 50ohm operation. No external matching component is required. It provides a typical gain of 30 dB and P₁ dB power of more than 29 dBm. Typical bias condition is 8V at 750 mA. The MMIC is packaged in a copper based ceramic 6 pins power package. The copper based carrier of the package allows direct soldering of the device to the PCB for proper heat sinking.

APPLICATIONS

- Ku Band VSAT Transmit Subsystem

LECTRICAL SPECIFICATIONS (Ta = 25 °C)

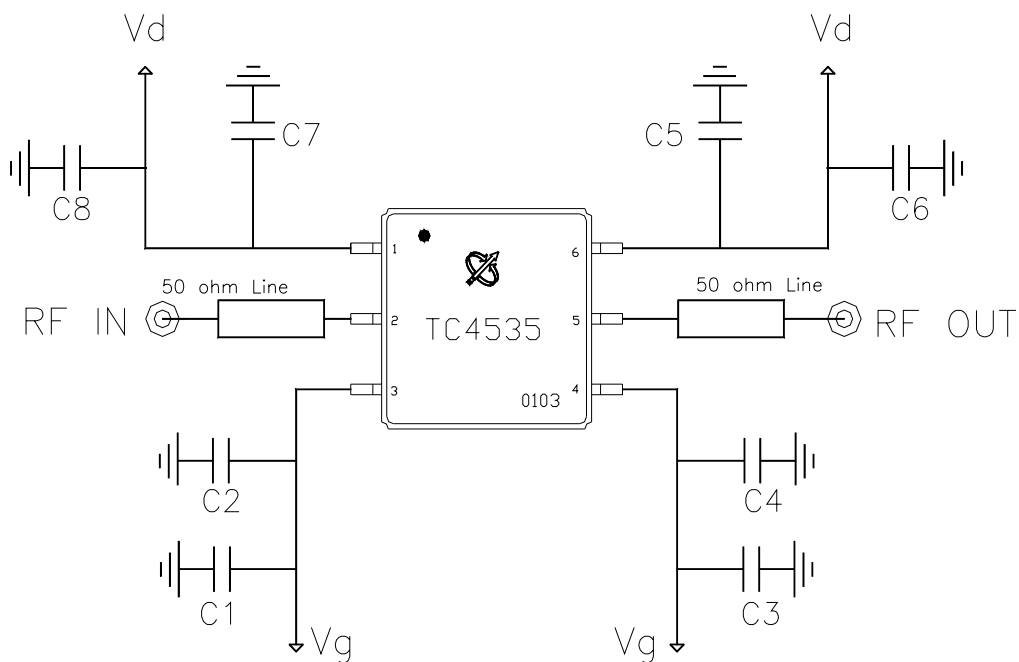
SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNITS
FREQ	Frequency Range	13.75		14.5	GHz
SSG	Small Signal Gain	29	30		dB
P₁ dB	Output Power at 1 dB Gain Compression	29	30		dBm
P₃ dB	Output Power at 3 dB Gain Compression	30	31		dBm
IP3	Third Order Intercept Point		39		dBm
VSWR, In	Input VSWR		2:1		-
VSWR, Out	Output VSWR		2.5:1		-
VDD	Supply Voltage		8		Volt
Vg	Gate Voltage	-0.5	-1.0	-1.5	Volt
IDD	Current Supply Without RF		750		mA
IDP₁	Current Supply @ Pout = P ₁ dB		750		mA

Absolute Maximum Ratings

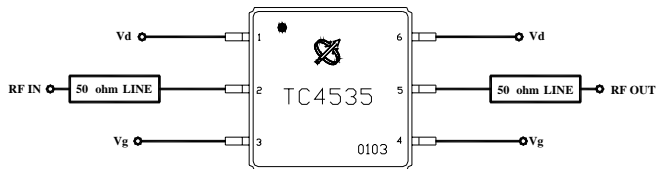
Symbol	Parameter/Conditions	Min.	Max.	Units
V_{dd}	Drain-Source Voltage		10	Volts
I_{dd}	Total Drain Current		1600	mA
P_{in}	RF Input Power		10	dBm
P_t	Power Dissipation		12	W
T_{ch}	Operating Channel Temperature		175	°C
T_{STG}	Storage Temperature	-65	175	°C

Note:

1. This GaAs MMIC is susceptible to damage from Electrostatic Discharge. Proper precautions should be used when handling these devices.
2. Specifications subject to change without notice.

TEST CIRCUITS
Evaluation Board Schematic


Part Type	Reference Designator	Description	Manufacturer	Part Number
Capacitor	C1, C3, C5, C7	1000pF 0603	Murata	GRM39C0G102J50V
Capacitor	C2, C4, C6, C8	0.1 uF 0603	Murata	GRM39Y5V104Z25V

CONNECTION DIAGRAM AND PIN DESCRIPTIONS


Pin #	Name	Description
2	RF IN	RF input (internally DC blocked)
1,6	Vd	MMIC drain bias
3,4	Vg	MMIC gate bias
5	RF OUT	RF output (internally DC blocked)

PHYSICAL DIMENSIONS (Unit: mil)
